

Low Voltage Quad 2-Input OR Gate with 5 V Tolerant Inputs

74LCX32

The LCX32 contains four 2-input OR gates. The inputs tolerate voltages up to 5.5 V allowing the interface of 5 V systems to 3 V systems.

The 74LCX32 is fabricated with advanced CMOS technology to achieve high speed operation while maintaining CMOS low power dissipation.

Features

- 5 V Tolerant Inputs
- 1.65 V 5.5 V V_{CC} Specifications Provided
- 5.5 ns t_{PD} Max. ($V_{CC} = 3.3 \text{ V}$), 10 mA I_{CC} Max.
- Power Down High Impedance Inputs and Outputs
- ±24 mA Output Drive (V_{CC} = 3.0 V)
- Implements Proprietary Noise/EMI Reduction Circuitry
- Latch-up Performance Exceeds JEDEC 78 Conditions
- ESD performance:
 - ♦ Human Body Model >2000 V
- Available on TSSOP WB and Leadless QFN Packages
- These are Pb-Free Devices

MARKING DIAGRAMS



TSSOP-14 DT SUFFIX CASE 948G



XXXXXX = Specific Device Code A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)



QFN14 3.0x2.5, 0.5P CASE 510CB

ZXYKK XXXXXX

XXXXXX = Specific Device Code
Z = Assembly Plant Code
XY = Date Code (Year & Week)
KK = Lot Run Traceability Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

CONNECTION DIAGRAMS

Figure 1. Pin Assignments for SOIC and TSSOP

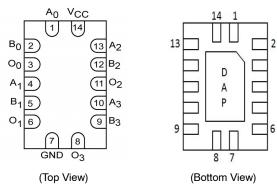


Figure 2. Pad Assignments for DQFN

LOGIC SYMBOL

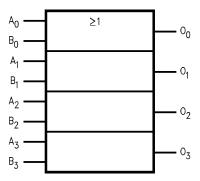


Figure 3. IEEE/IEC

PIN DESCRIPTION

Pin Names	Description
A _n , B _n	Inputs
O _n	Outputs
DAP	No Connect

1. DAP (Die Attach Pad)

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +6.5	V
VI	DC Input Voltage (Note 1)		-0.5 to +6.5	V
Vo		ive-Mode (High or Low State) Tri-State Mode ower-Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +6.5 -0.5 to +6.5	V
I _{IK}	DC Input Diode Current	V _I < GND	-50	mA
lok	DC Output Diode Current	V _O < GND	-50	mA
Io	DC Output Source/Sink Current		±50	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or Ground Pin		±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 secs		260	°C
TJ	Junction Temperature Under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 1)	QFN14 TSSOP-14	130 150	°C/W
P _D	Power Dissipation in Still Air at 125°C	QFN14 TSSOP-14	962 833	mW
MSL	Moisture Sensitivity		Level 1	_
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	_
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 N/A	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- I_O absolute maximum rating must be observed.
 Measured with minimum pad spacing on an FR4 board, using 76 mm-by-114 mm, 2-ounce copper trace no air flow per JESD51-7.
 HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.

RECOMMENDED OPERATING CONDITIONS

Symbol	Р	arameter	Min	Тур	Max	Unit
V_{CC}	Supply Voltage	Operating	1.65	3.3	5.5	V
		Data Retention Only	1.5	3.3	5.5	
VI	Digital Input Voltage		0	_	5.5	V
Vo	Output Voltage	Active Mode (High or Low State)	0	-	V_{CC}	V
		Tri-State Mode	0	_	5.5	
		Power Down Mode (V _{CC} = 0 V)	0	_	5.5	
T _A	Operating Free-Air Temperature		-40	_	+125	°C
t _r , t _f	Input Rise or Fall Rate	V _{CC} = 1.65 V to 1.95 V	0	-	20	nS/V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0	_	20	
		V_I from 0.8 V to 2.0 V, V_{CC} = 3.0 V	0	_	10	
		V_{CC} = 4.5 V to 5.5 V	0	_	5	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

4. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS

				T _A = -40°0	C to +85°C	T _A = -40°C	to +125°C	
Symbol	Parameter	Conditions	V _{CC} (V)	Min	Max	Min	Max	Unit
V _{IH}	HIGH Level Input Voltage		1.65 – 1.95	0.65 x V _{CC}	-	0.65 x V _{CC}	-	٧
			2.3 – 2.7	1.7	-	1.7	-	
			3.0 – 3.6	2.0	-	2.0	-	
			4.5 – 5.5	0.70 x V _{CC}	-	0.70 x V _{CC}	-	
V _{IL}	LOW Level Input Voltage		1.65 – 1.95	-	0.35 x V _{CC}	-	0.35 x V _{CC}	V
			2.3 – 2.7	_	0.7	-	0.7	
			3.0 – 3.6	-	0.8	-	0.8	
			4.5 – 5.5	-	0.30 x V _{CC}	_	0.30 x V _{CC}	
V _{OH}	High-Level Output Voltage Low-Level Output Voltage	$\begin{split} V_I &= V_{IH} \text{ or } V_{IL} \\ I_{OH} &= -100 \mu\text{A} \\ I_{OH} &= -4 \text{ mA} \\ I_{OH} &= -8 \text{ mA} \\ I_{OH} &= -12 \text{ mA} \\ I_{OH} &= -16 \text{ mA} \\ I_{OH} &= -24 \text{ mA} \\ I_{OH} &= -32 \text{ mA} \\ \end{split}$ $V_I &= V_{IH} \text{ or } V_{IL} \\ I_{OL} &= 100 \mu\text{A} \\ I_{OL} &= 4 \text{ mA} \\ I_{OL} &= 8 \text{ mA} \\ I_{OL} &= 12 \text{ mA} \\ I_{OL} &= 16 \text{ mA} \\ I_{OL} &= 24 \text{ mA} \\ I_{OL$	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5 1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	V _{CC} - 0.1 1.29 1.8 2.2 2.4 2.2 3.7	- - - - - - 0.1 0.24 0.3 0.4 0.4 0.55 0.6	V _{CC} - 0.1 1.29 1.8 2.2 2.4 2.2 3.7	- - - - - - 0.1 0.24 0.3 0.4 0.4 0.55 0.6	V
II	Input Leakage Current	$I_{OL} = 32 \text{ mA}$ $V_{I} = 0 \text{ to } 5.5 \text{ V}$	1.65 – 5.5	_	±5.0	_	±5.0	μΑ
l _{OFF}	Power Off Leakage Current	$V_I = 5.5 \text{ V or}$ $V_O = 5.5 \text{ V}$	0	-	10	_	10	μΑ
I _{CC}	Quiescent Supply Current	V _I = 5.5 V or GND	1.65 – 5.5	-	10	-	10	μΑ
ΔI_{CC}	Increase in I _{CC} per Input	V _{IH} = V _{CC} - 0.6 V	2.3 to 3.6	_	500	_	500	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

				T _A = -40°C	c to +85°C	T _A = -40°C	to +125°C	
Symbol	Parameter	Test Condition	V _{CC} (V)	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay, Input to Output	See Figures 4 and 5	1.65 to 1.95	-	9.8	-	9.8	ns
			2.3 to 2.7	-	6.6	-	6.6	
			2.7	-	6.2	-	6.2	
			3.0 to 3.6	-	5.5	_	5.5	
			4.5 to 5.5	-	4.0	_	4.0	

AC ELECTRICAL CHARACTERISTICS

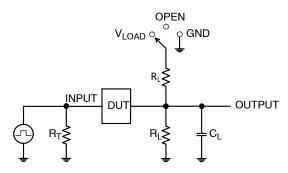
				T _A = -40°C	C to +85°C	T _A = -40°C	to +125°C		
Symbol	Parameter	Test Condition	V _{CC} (V)	Min	Max	Min	Max	Unit	
t _{OSHL} , t _{OSLH}				1.65 to 1.95	-	-	-	-	ns
			2.3 to 2.7	-	-	-	-		
			2.7	-	-	-	-		
			3.0 to 3.6	-	1.0	-	1.0		
			4.5 to 5.5	-	_	-	-		

DYNAMIC SWITCHING CHARACTERISTICS

				T _A = 25°C	
Symbol	Parameter	V _{CC} (V)	Conditions	Typical	Unit
V _{OLP}	Quiet Output Dynamic Peak V _{OL}	3.3	C _L = 50 pF, V _{IH} = 3.3 V, V _{IL} = 0 V	0.8	V
		2.5	C _L = 30 pF, V _{IH} = 2.5 V, V _{IL} = 0 V	0.6	
V _{OLV}	Quiet Output Dynamic Valley V _{OL}	3.3	C _L = 50 pF, V _{IH} = 3.3 V, V _{IL} = 0 V	-0.8	V
		2.5	C _L = 30 pF, V _{IH} = 2.5 V, V _{IL} = 0 V	-0.6	

CAPACITANCE

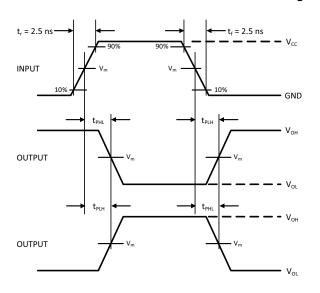
Symbol	Parameter	Conditions	Typical	
C _{IN}	Input Capacitance	V _{CC} = Open, V _I = 0 V or V _{CC}	7	pF
C _{OUT}	Output Capacitance	$V_{CC} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	8	pF
C _{PD}	Power Dissipation Capacitance	V _{CC} = 3. 3 V, V _I = 0 V or V _{CC} , f = 10 MHz	25	pF

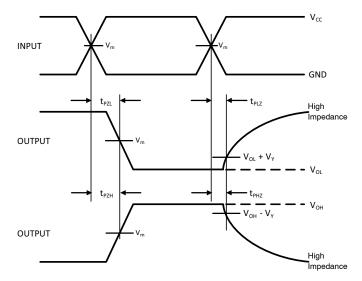


Test	Switch Position
t _{PLH} / t _{PHL}	Open
t _{PLZ} / t _{PZL}	V_{LOAD}
t _{PHZ} / t _{PZH}	GND

 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$ f = 1 MHz

Figure 4. Test Circuit





V _{CC} , V	R _L , Ω	C _L , pF	V _{LOAD}	V _m , V	V _Y , V
1.65 to 1.95	500	30	2 x V _{CC}	V _{CC} /2	0.15
2.3 to 2.7	500	30	2 x V _{CC}	V _{CC} /2	0.15
2.7	500	50	6 V	1.5	0.3
3.0 to 3.6	500	50	6 V	1.5	0.3
4.5 to 5.5	500	50	2 x V _{CC}	V _{CC} /2	0.3

Figure 5. Switching Waveforms

SCHEMATIC DIAGRAM (GENERIC FOR LCX FAMILY)

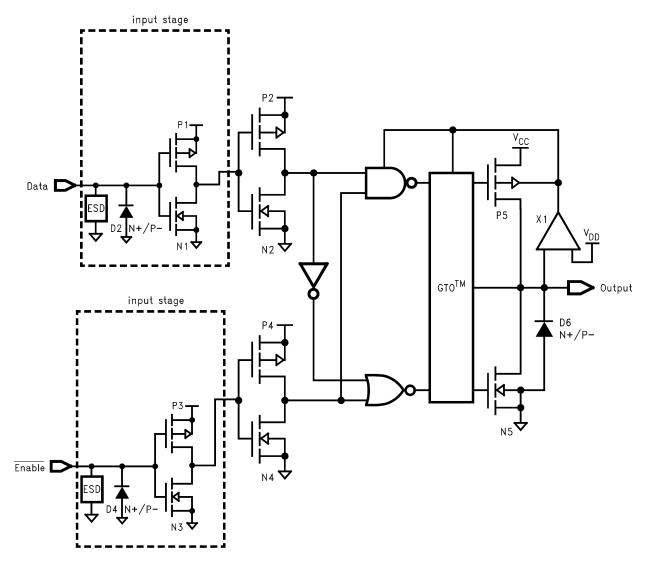


Figure 6. Schematic Diagram (Generic for LCX Family)

ORDERING INFORMATION

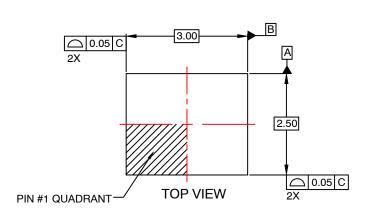
Device	Marking	Package	Shipping [†]
74LCX32MTCX	LCX 32	TSSOP-14	2500 / Tape & Reel
74LCX32BQX	LCX32	QFN-14	3000 / Tape & Reel

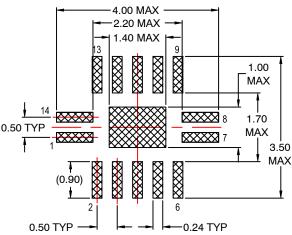
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



QFN14 3.0x2.5, 0.5P CASE 510CB ISSUE O

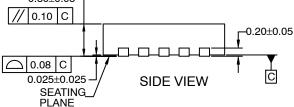
DATE 31 AUG 2016

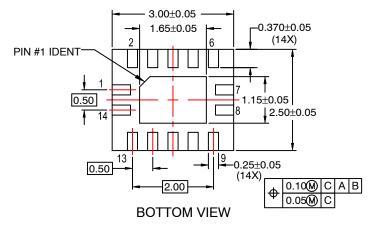




RECOMMENDED LAND PATTERN

0.80±0.05-// 0.10 C _____ 0.08 C c 0.025±0.025 SIDE VIEW SEATING





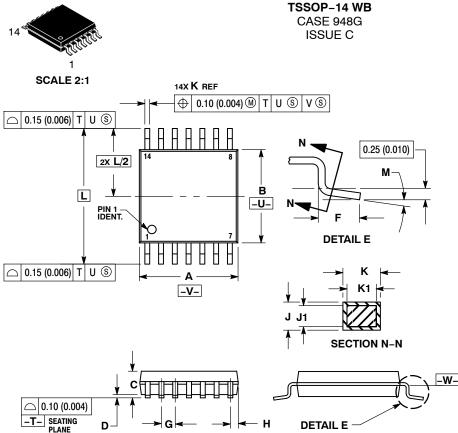
NOTES:

- A. CONFORMS TO JEDEC REGISTRATION MO-241, VARIATION AA
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

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DATE 17 FEB 2016

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 TERMINAL NUMBERS ARE SHOWN FOR DEEEDENIC OMITY.
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
м	o °	8 °	o °	a °

GENERIC MARKING DIAGRAM*



= Assembly Location

L = Wafer Lot = Year

= Work Week W

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*

-	7.06
1	
	
	0.65 PITCH
↓ □	
14X 0.36 126	
0.36 - 1.26	DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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